

### **Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application.

### **Listing of Claims:**

Claim 1 (currently amended): A capacitive structure, comprising:

- a semiconductor base region having an upper surface;
- a well formed within the semiconductor base region and adjacent the upper surface;
- a first dielectric layer adjacent at least a portion of the upper surface;
- a polysilicon layer adjacent the first dielectric layer, wherein the well, the first dielectric layer, and the first polysilicon layer form a first capacitor and are aligned along a planar dimension;
- a first conductive layer positioned with at least a portion overlying at least a portion of the polysilicon layer and electrically connected to said polysilicon layer;
- a second dielectric layer adjacent the first conductive layer; and
- a second conductive layer adjacent the second dielectric layer with a first electrical connection to said well, wherein the first conductive layer, the second dielectric layer, and the second conductive layer form a second capacitor and are aligned along the planar dimension-; and
  - said first electrical connection further comprising:
    - a first metal layer comprising a first region and a second region electrically separate from the first region, wherein the first region is adjacent the second conductive layer;
    - a second metal layer at a distance greater than a distance between the upper surface and the first region of the first metal layer;
    - a second electrical connection between the first region of the first metal layer and the second metal layer;

a third electrical connection between the second metal layer and the second region of the first metal layer; and

a fourth electrical connection between the second region of the first metal layer and the well.

Claim 2 (canceled)

Claim 3 (currently amended): The capacitive structure of claim 1 2:

wherein the first conductive layer has a first side adjacent the second dielectric layer and a second side facing in a direction toward the upper surface; and

wherein the electrical connection contacts the second side of the first conductive layer.

Claim 4 (original): The capacitive structure of claim 3 wherein the electrical connection is substantially perpendicular to the planar dimension.

Claim 5 (canceled)

Claim 6 (currently amended): The capacitive structure of claim 1 5:

wherein the well comprises a length having a first end and a second end;

wherein the second electrical connection is between the second conductive layer and the first end of the well; and

wherein the second end of the well is for connecting to a fixed potential.

Claim 7 (original): The capacitive structure of claim 6 wherein the fixed potential is ground.

Claim 8 (original): The capacitive structure of claim 6:

wherein the fixed potential equals a first fixed potential; and

wherein the first electrical connection is for connecting to a second fixed potential that is unequal to the first fixed potential.

Claim 9 (canceled)

Claim 10 (currently amended): The capacitive structure of claim 1 9:

wherein the second conductive layer has a first length in a first dimension along the planar dimension and a first width in a second dimension along the planar dimension that is perpendicular to the first length;

wherein the first region of the first metal layer has a second length, less than the first length, and in the first dimension; and

wherein the first region of the first metal layer has a second width, less than the first width, and in the second dimension.

Claim 11 (original): The capacitive structure of claim 10 wherein the first conductive layer and the second conductive layer comprise TaN.

Claim 12 (original): The capacitive structure of claim 10 wherein the second dielectric comprises Ta<sub>2</sub>O<sub>5</sub>.

Claim 13 (original): The capacitive structure of claim 10:

wherein the first conductive layer and the second conductive layer comprise TaN;  
and

wherein the second dielectric comprises Ta<sub>2</sub>O<sub>5</sub>.

Claim 14 (original): The capacitive structure of claim 10 wherein the second dielectric comprises a dielectric constant greater than 4.0.

Claim 15 (original): The capacitive structure of claim 10 wherein the second capacitor has a capacitance greater than a capacitance of the second capacitor.

Claim 16 (original): The capacitive structure of claim 1 wherein the semiconductor base region is selected from a set consisting of a semiconductor well and a semiconductor substrate.

Claim 17 (original): The capacitive structure of claim 1:

wherein the second conductive layer has a first length in a first dimension along the planar dimension and a first width in a second dimension along the planar dimension that is perpendicular to the first length;

wherein the first region of the first metal layer has a second length, less than the first length, and in the first dimension; and

wherein the first region of the first metal layer has a second width, less than the first width, and in the second dimension.

Claim 18 (original): The capacitive structure of claim 1 wherein the first conductive layer and the second conductive layer comprise TaN.

Claim 19 (original): The capacitive structure of claim 1 wherein the second dielectric comprises Ta<sub>2</sub>O<sub>5</sub>.

Claim 20 (original): The capacitive structure of claim 1:

wherein the first conductive layer and the second conductive layer comprise TaN;  
and

wherein the second dielectric comprises Ta<sub>2</sub>O<sub>5</sub>.

Claim 21 (original): The capacitive structure of claim 1 wherein the second dielectric comprises a dielectric constant greater than 4.0.

Claim 22 (original): The capacitive structure of claim 21 wherein the second capacitor has a capacitance greater than a capacitance of the second capacitor.

Claims 23-34 (canceled)